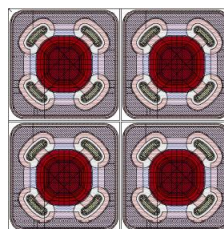


Wafer Information

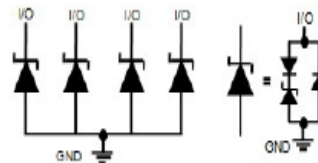
Item	Description
Wafer Size	6 inch (150mm)
Wafer Thickness	150um ± 10um
Die Size (with scribe lane)	334um x 334um
Bond Pad Opening	71um x 71um
Scribe Lane Width	40um
Gross Die Per Wafer	143,000
Top Metal (for wire bond)	4µm AlSiCu
Backside Metal (for die bond)	Ag

- Complies with IEC 61000-4-2 standards:
Contact discharge: ±20kV

Die Appearance



Circuit Diagram



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	75	W
Peak Pulse Current (8/20µs)	IPP	5	A
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	6.0			V	I _T = 1mA
Reverse Leakage Current	I _R			100	nA	VRWM = 5V
Forward voltage	V _F			1.2	V	I _F = 15mA
Clamping Voltage	V _C			9.8	V	I _{PP} = 1A (8 x 20µs pulse)
Clamping Voltage	V _C			15	V	I _{PP} = 5A (8 x 20µs pulse)
Junction Capacitance	C _J		0.45	0.60	pF	V _R = 0V, f = 1MHz, I/O to GND
Junction Capacitance	C _J		0.22	0.30	pF	V _R = 0V, f = 1MHz, IO to IO

Note: Electrical parameters are only for die, performance may alter after assembly.

NOTICE

Leiditech reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Leiditech does not assume any liability arising out of the application or use of any product described herein.